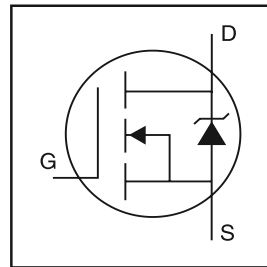


IRFZ34NPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Lead-Free

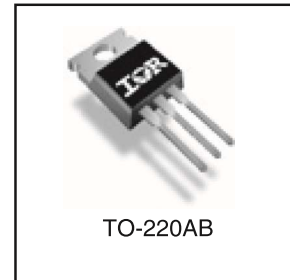


| |
|----------------------------|
| $V_{DSS} = 55V$ |
| $R_{DS(on)} = 0.040\Omega$ |
| $I_D = 29A$ |

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---------------------------|--|--------------------|-------|
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 29 | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 20 | |
| I_{DM} | Pulsed Drain Current $\text{\textcircled{1}}$ | 100 | |
| $P_D @ T_C = 25^\circ C$ | Power Dissipation | 68 | W |
| | Linear Derating Factor | 0.45 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulse Avalanche Energy $\text{\textcircled{2}}$ | 65 | mJ |
| I_{AR} | Avalanche Current $\text{\textcircled{2}}$ | 16 | A |
| E_{AR} | Repetitive Avalanche Energy $\text{\textcircled{2}}$ | 6.8 | mJ |
| dv/dt | Peak Diode Recovery dv/dt $\text{\textcircled{3}}$ | 5.0 | V/ns |
| T_J | Operating Junction and Storage Temperature Range | -55 to + 175 | °C |
| T_{STG} | | | |
| | | | |
| | Mounting torque, 6-32 or M3 screw | 10 lbf•in (1.1N•m) | |

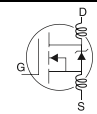
Thermal Resistance

| | Parameter | Min. | Typ. | Max. | Units |
|-----------------|-------------------------------------|------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case | — | — | 2.2 | °C/W |
| $R_{\theta CS}$ | Case-to-Sink, Flat, Greased Surface | — | 0.50 | — | |
| $R_{\theta JA}$ | Junction-to-Ambient | — | — | 62 | |

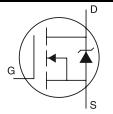
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International
IR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------------------------|--------------------------------------|------|-------|-------|----------|---|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | 55 | — | — | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.052 | — | V/°C | Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ |
| $R_{DS(ON)}$ | Static Drain-to-Source On-Resistance | — | — | 0.040 | Ω | $V_{GS} = 10V, I_D = 16A$ ③ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 2.0 | — | 4.0 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| g_{fs} | Forward Transconductance | 6.5 | — | — | S | $V_{DS} = 25V, I_D = 16A$ |
| I_{DSS} | Drain-to-Source Leakage Current | — | — | 25 | μA | $V_{DS} = 55V, V_{GS} = 0V$ |
| | | — | — | 250 | | $V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$ |
| I_{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | $V_{GS} = 20V$ |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | $V_{GS} = -20V$ |
| Q_g | Total Gate Charge | — | — | 34 | nC | $I_D = 16A$ |
| Q_{gs} | Gate-to-Source Charge | — | — | 6.8 | | $V_{DS} = 44V$ |
| Q_{gd} | Gate-to-Drain ("Miller") Charge | — | — | 14 | | $V_{GS} = 10V$, See Fig. 6 and 13 ④ |
| $t_{d(on)}$ | Turn-On Delay Time | — | 7.0 | — | ns | $V_{DD} = 28V$ |
| t_r | Rise Time | — | 49 | — | | $I_D = 16A$ |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 31 | — | | $R_G = 18\Omega$ |
| t_f | Fall Time | — | 40 | — | | $R_D = 1.8\Omega$, See Fig. 10 ④ |
| L_D | Internal Drain Inductance | — | 4.5 | — | nH | Between lead, 6mm (0.25in.) from package and center of die contact |
| L_S | Internal Source Inductance | — | 7.5 | — | |  |
| C_{iss} | Input Capacitance | — | 700 | — | pF | $V_{GS} = 0V$ |
| C_{oss} | Output Capacitance | — | 240 | — | | $V_{DS} = 25V$ |
| C_{riss} | Reverse Transfer Capacitance | — | 100 | — | | $f = 1.0\text{MHz}$, See Fig. 5 |

Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------|--|---|------|------|-------|--|
| I_S | Continuous Source Current (Body Diode) | — | — | 29 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I_{SM} | Pulsed Source Current (Body Diode) ① | — | — | 100 | | |
| V_{SD} | Diode Forward Voltage | — | — | 1.6 | V | $T_J = 25^\circ\text{C}, I_S = 16A, V_{GS} = 0V$ ④ |
| t_{rr} | Reverse Recovery Time | — | 57 | 86 | ns | $T_J = 25^\circ\text{C}, I_F = 16A$ |
| Q_{rr} | Reverse Recovery Charge | — | 130 | 200 | nC | $di/dt = 100A/\mu s$ ④ |
| t_{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$) | | | | |

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 410\mu H$, $R_G = 25\Omega$, $I_{AS} = 16A$. (See Figure 12)
- ③ $I_{SD} \leq 16A$, $di/dt \leq 420A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

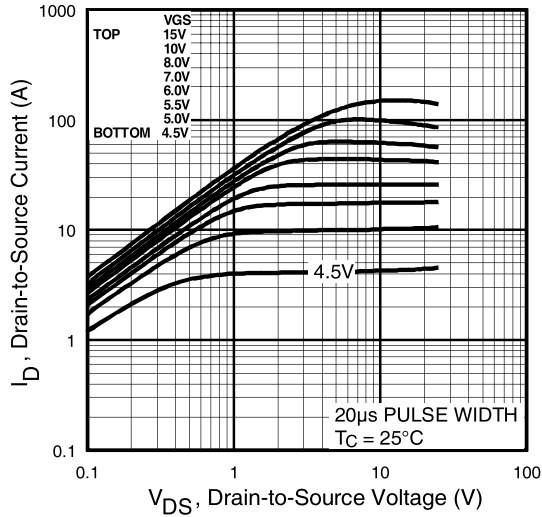


Fig 1. Typical Output Characteristics

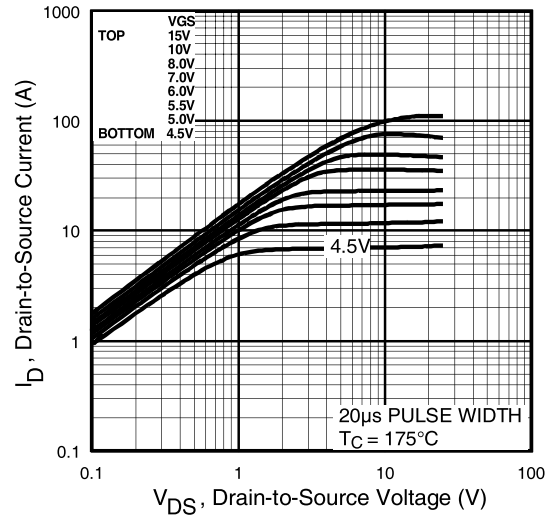


Fig 2. Typical Output Characteristics

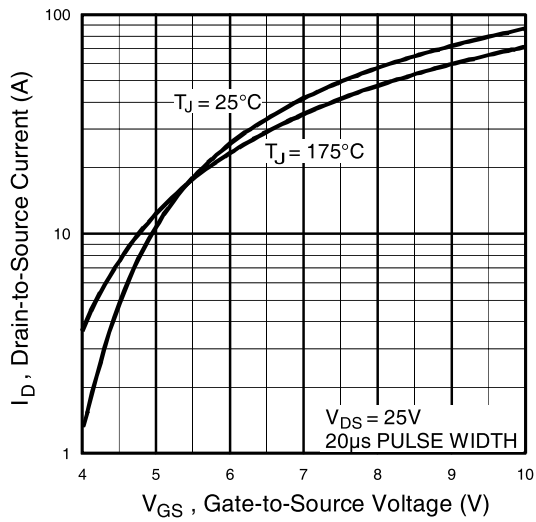


Fig 3. Typical Transfer Characteristics

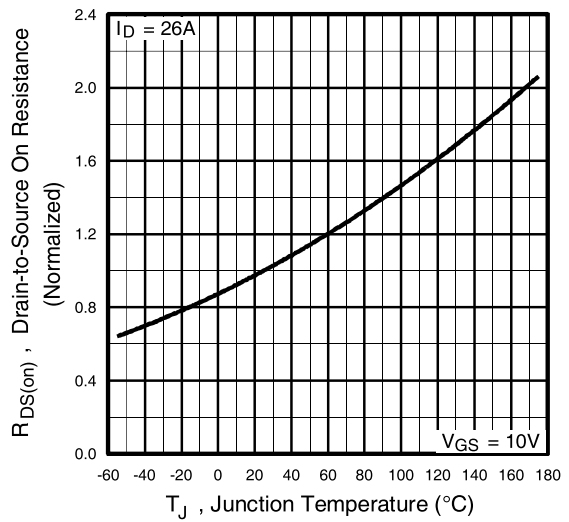


Fig 4. Normalized On-Resistance Vs. Temperature

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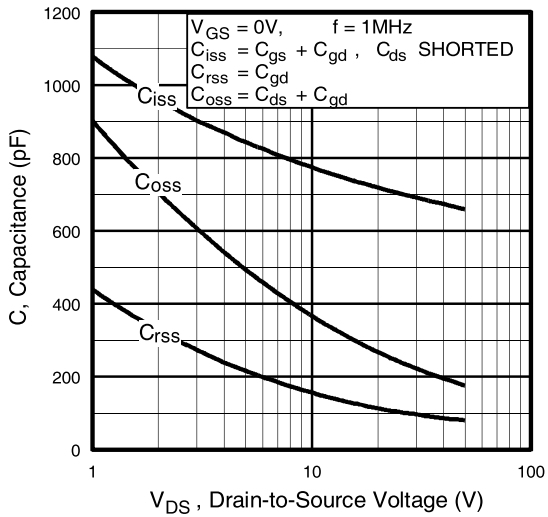


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

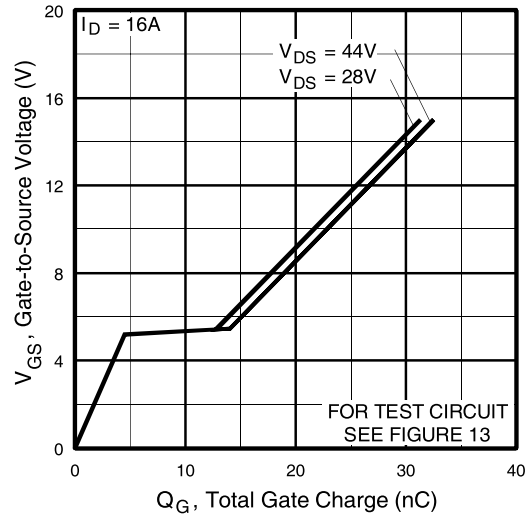


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

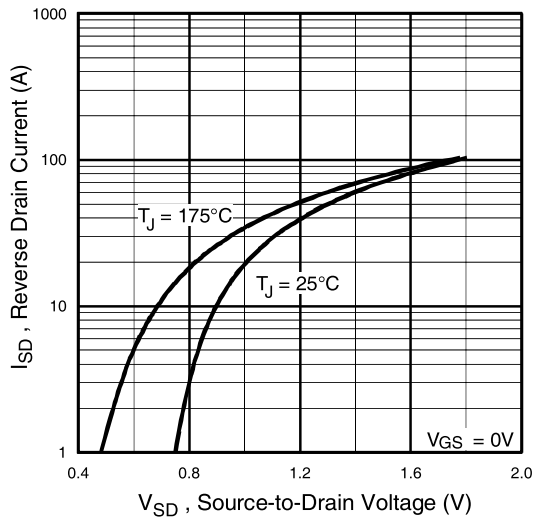


Fig 7. Typical Source-Drain Diode Forward Voltage

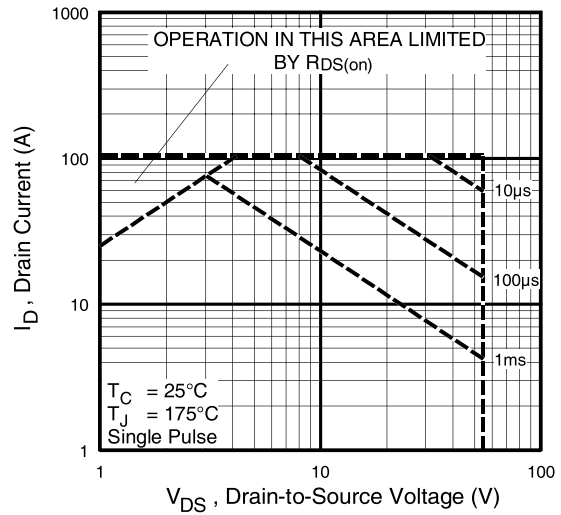


Fig 8. Maximum Safe Operating Area

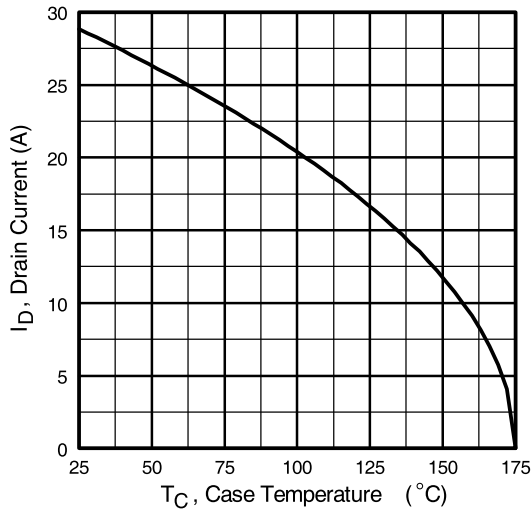


Fig 9. Maximum Drain Current Vs. Case Temperature

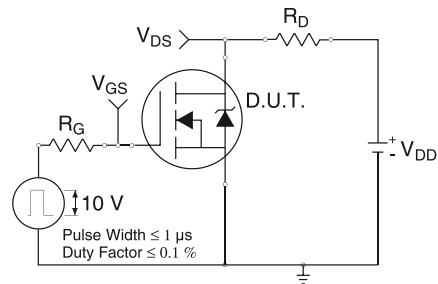


Fig 10a. Switching Time Test Circuit

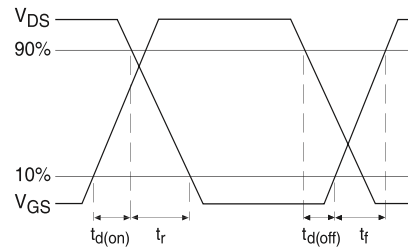


Fig 10b. Switching Time Waveforms

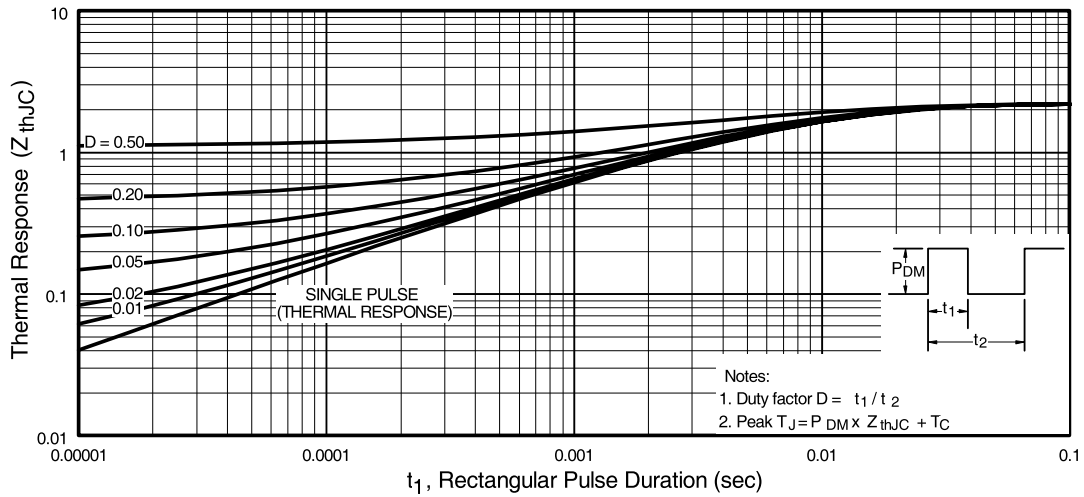


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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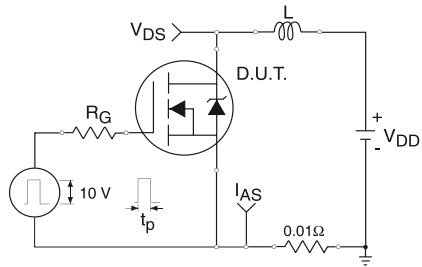


Fig 12a. Unclamped Inductive Test Circuit

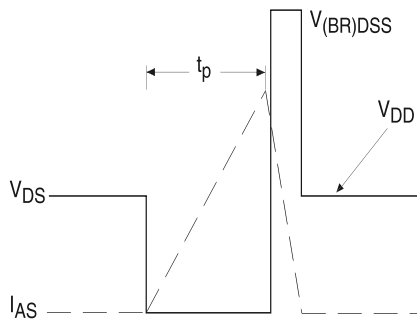


Fig 12b. Unclamped Inductive Waveforms

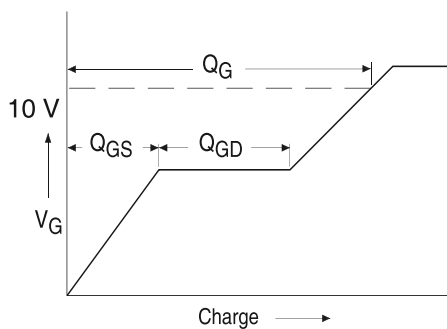


Fig 13a. Basic Gate Charge Waveform

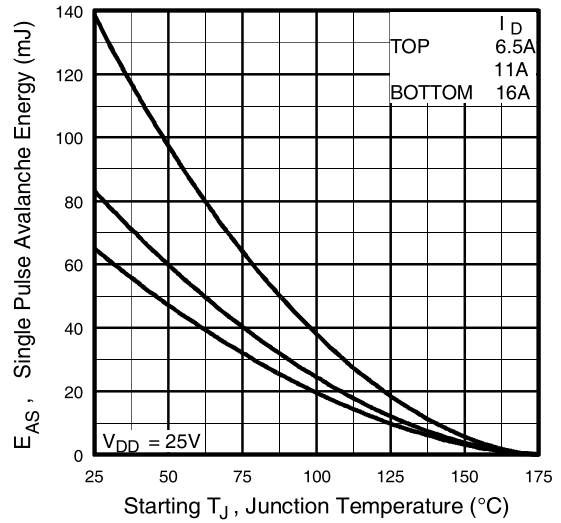


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

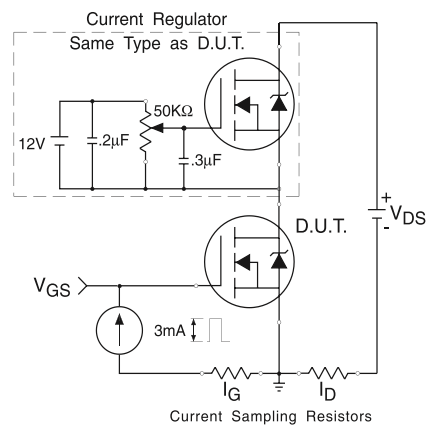
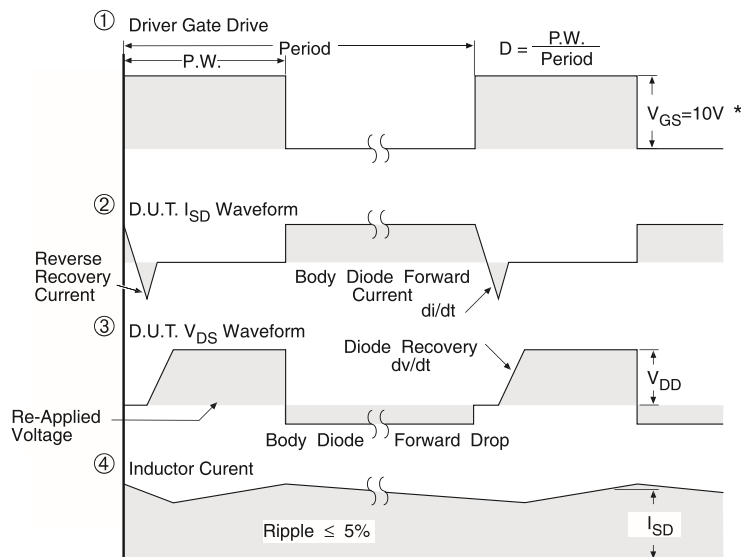
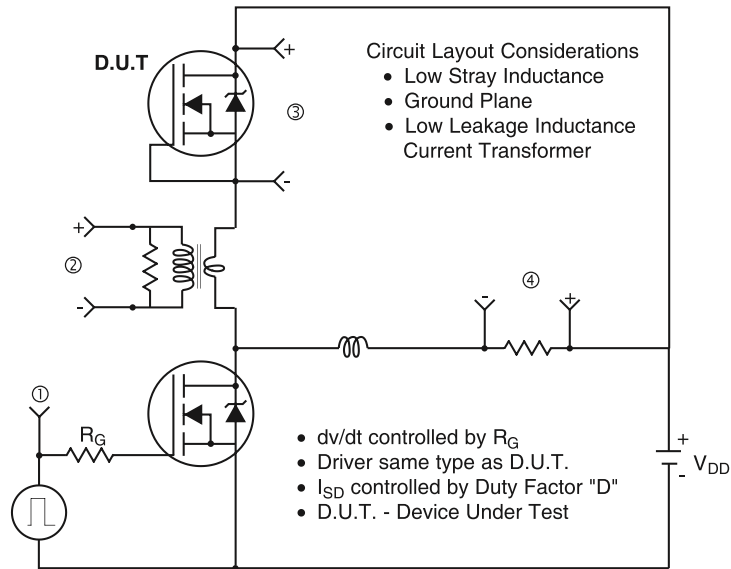


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

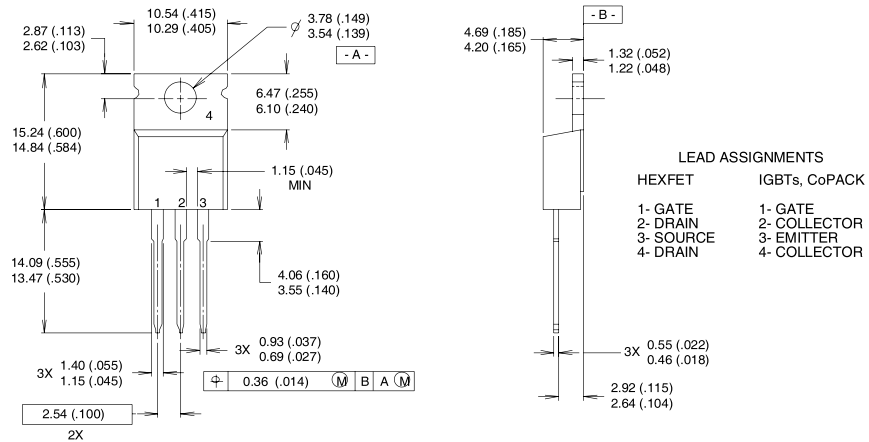
Fig 14. For N-Channel HEXFETS

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TO-220AB Package Outline

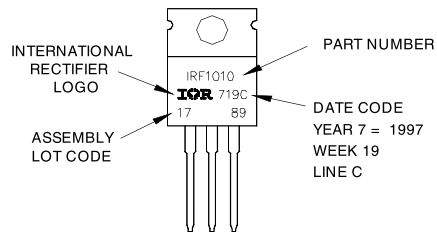
Dimensions are shown in millimeters (inches)



- NOTES:
- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
 - 2 CONTROLLING DIMENSION : INCH
 - 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
 - 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line
 position indicates "Lead-Free"



Data and specifications subject to change without notice.



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.10/03

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>